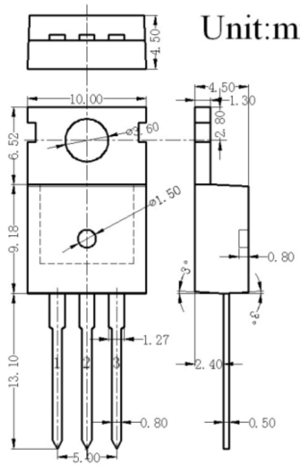
SHEN ZHEN LONG JING MICRO- ELECTRONICS CO.， LTD

TO-220 Plastic-Encapsulate MOSFETS

IRF9520

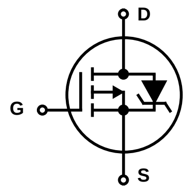
Unit:mm



1、 GATE

2、 DRAIN

3、 SOURCE



6A, 100V, 0.600 Ohm, P-Channel Power MOSFET

This advanced power MOSFET is designed, tested, and guaranteed to withstand a specified level of energy in the breakdown avalanche mode of operation. These are P-Channel enhancement mode silicon gate power field effect transistors designed for applications such as switching regulators, switching converters, motor drivers, relay drivers and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. These types can be operated directly from integrated circuits.

Formerly developmental type TA17501.

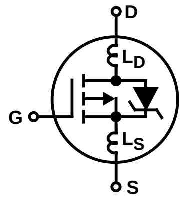
Features

- 6A, 100V
- $r_{DS(ON)} = 0.600\Omega$
- Single Pulse Avalanche Energy Rated
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance

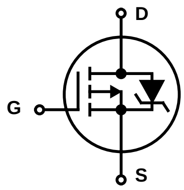
Absolute Maximum Ratings $T_C = 25^oC$, Unless Otherwise Specified

		IRF9520	UNITS
Drain to Source Breakdown Voltage (Note 1)	V_{DS}	-100	V
Drain to Gate Voltage (R_{GS} = 20kΩ) (Note 1)	V_{DGR}	-100	V
Continuous Drain Current	I_D	-6	A
$T_C = 100^oC$	I_D	-4	A
Pulsed Drain Current (Note 3)	I_{DM}	-24	A
Gate to Source Voltage	V_{GS}	±20	V
Maximum Power Dissipation (Figure 1)	P_D	40	W
Linear Derating Factor (Figure 1)		0.32	$W/^oC$
Single Pulse Avalanche Energy Rating (Note 4)	E_{AS}	370	mJ
Operating and Storage Temperature	T_J, T_{STG}	-55 to 150	^oC
Maximum Temperature for Soldering			
Leads at 0.063in (1.6mm) from Case for 10s	T_L	300	^oC
Package Body for 10s, See Techbrief 334	T_{pkg}	260	^oC

Electrical Specifications $T_C = 25^oC$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV_{DSS}	$I_D = -250\mu A$, $V_{GS} = 0V$ (Figure 10)	-100	-	-	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = -250\mu A$	-2	-	-4	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = Rated BV_{DSS}, $V_{GS} = 0V$	-	-	-25	µA
		V_{DS} = 0.8 x Rated BV_{DSS}, $V_{GS} = 0V$ $T_C = 125^oC$	-	-	-250	µA
On-State Drain Current (Note 2)	$I_{D(ON)}$	$V_{DS} > I_{D(ON)} \times r_{DS(ON)\ MAX}$, $V_{GS} = -10V$	-6	-	-	A
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V$	-	-	±100	nA
Drain to Source On Resistance (Note 2)	$r_{DS(ON)}$	$I_D = -3.5A$, $V_{GS} = -10V$ (Figures 8, 9)	-	0.500	0.600	Ω
Forward Transconductance (Note 2)	g_{fs}	$V_{DS} > I_{D(ON)} \times r_{DS(ON)MAX}$, $I_D = -3.5A$ (Figure 12)	0.9	2	-	S
Turn-On Delay Time	$t_{d(ON)}$	V_{DD} = 0.5 x Rated BV_{DSS}, $I_D \approx -6.0A$, $R_G = 50\Omega$, $R_L = 7.7\Omega$ for $V_{DSS} = 50\Omega$ MOSFET Switching Times are Essentially Independent of Operating Temperature	-	25	50	ns
Rise Time	t_r		-	50	100	ns
Turn-Off Delay Time	$t_{d(OFF)}$		-	50	100	ns
Fall Time	t_f		-	50	100	ns
Total Gate Charge (Gate to Source + Gate to Drain)	$Q_{g(TOT)}$	$V_{GS} = -10V$, $I_D = -6A$, V_{DS} = 0.8 x Rated BV_{DSS} (Figure 14) Gate Charge is Essentially Independent of Operating Temperature	-	16	22	nC
Gate to Source Charge	Q_{gs}		-	9	-	nC
Gate to Drain "Miller" Charge	Q_{gd}		-	7	-	nC
Input Capacitance	C_{ISS}	$V_{DS} = -25V$, $V_{GS} = 0V$, f = 1MHz (Figure 11)	-	300	-	pF
Output Capacitance	C_{OSS}		-	200	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	50	-	pF
Internal Drain Inductance	L_D	Measured From the Contact Screw on Tab To Center of Die Modified MOSFET Symbol Showing the Internal Devices Inductances	-	3.5	-	nH
		Measured From the Drain Lead, 6mm (0.25in) from Package to Center of Die	-	4.5	-	nH
Internal Source Inductance	L_S	Measured From the Source Lead, 6mm (0.25in) From Header to Source Bonding Pad 	-	7.5	-	nH
Thermal Resistance Junction-to-Case	$R_{\theta JC}$		-	-	3.12	$^oC/W$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	Typical Socket Mount	-	-	62.5	$^oC/W$

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Continuous Source to Drain Current	I_{SD}	Modified MOSFET Symbol Showing the Integral Reverse P-N Junction Diode 	-	-	-6.0	A
Pulse Source to Drain Current (Note 3)	I_{SDM}		-	-	-24	A
Source to Drain Diode Voltage (Note 2)	V_{SD}	$T_C = 25^oC$, $I_{SD} = -6.0A$, $V_{GS} = 0V$ (Figure 13)	-	-	-1.5	V
Reverse Recovery Time	t_{rr}	$T_J = 150^oC$, $I_{SD} = -6.0A$, $dI_{SD}/dt = 100A/\mu s$	-	230	-	ns
Reverse Recovery Charge	Q_{RR}	$T_J = 150^oC$, $I_{SD} = -6.0A$, $dI_{SD}/dt = 100A/\mu s$	-	1.3	-	µC

NOTES:

2. Pulse test: pulse width ≤ 300µs, duty cycle ≤ 2%.
3. Repetitive rating: pulse width limited by maximum junction temperature. See Transient Thermal Impedance curve (Figure 3).
4. $V_{DD} = 25V$, starting $T_J = 25^oC$, L = 15.4mH, $R_G = 25\Omega$, peak $I_{AS} = 6.0A$.

Typical Performance Curves Unless Otherwise Specified

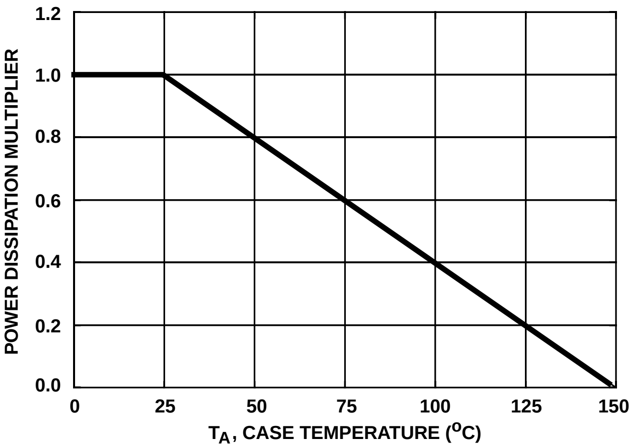


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

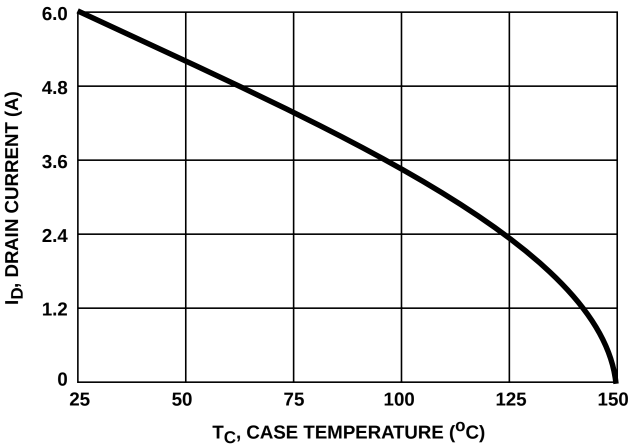


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

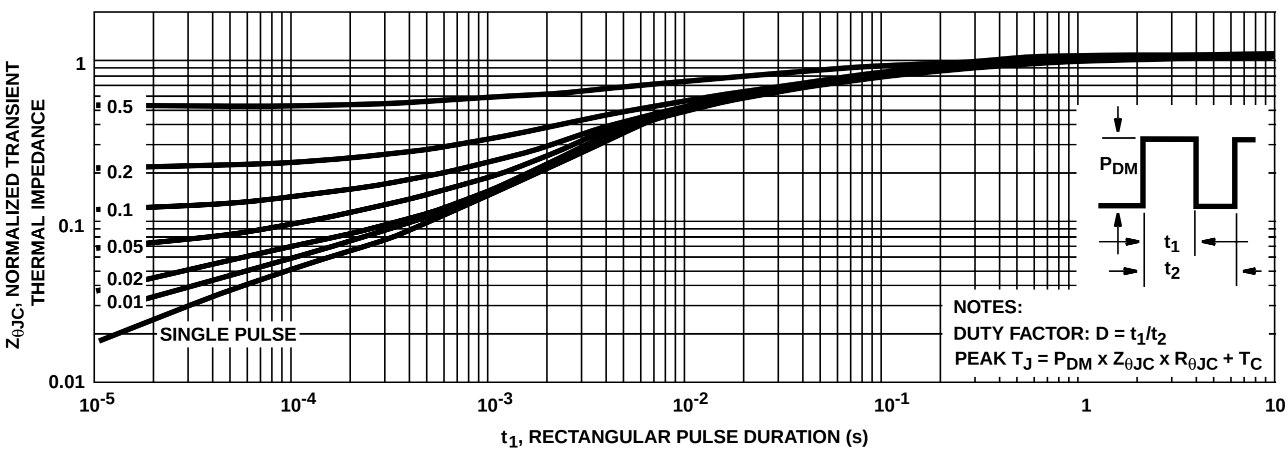


FIGURE 3. NORMALIZED TRANSIENT THERMAL IMPEDANCE

Typical Performance Curves Unless Otherwise Specified **(Continued)**

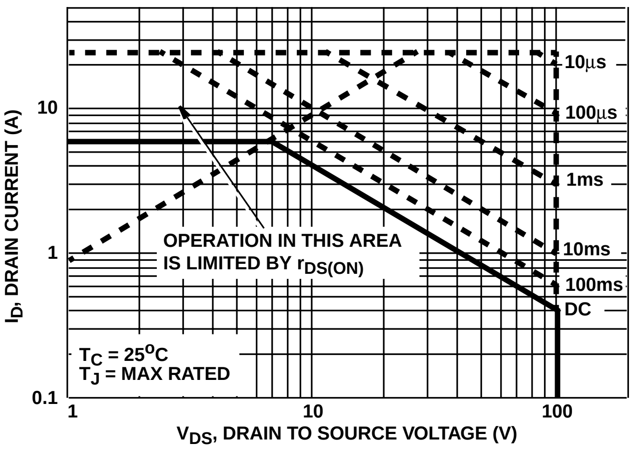


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

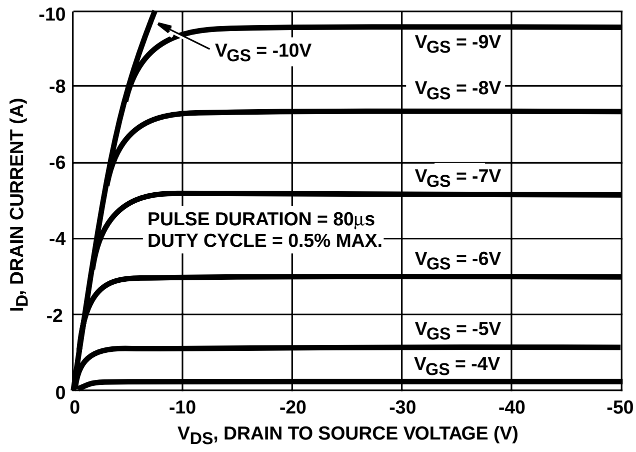


FIGURE 5. OUTPUT CHARACTERISTICS

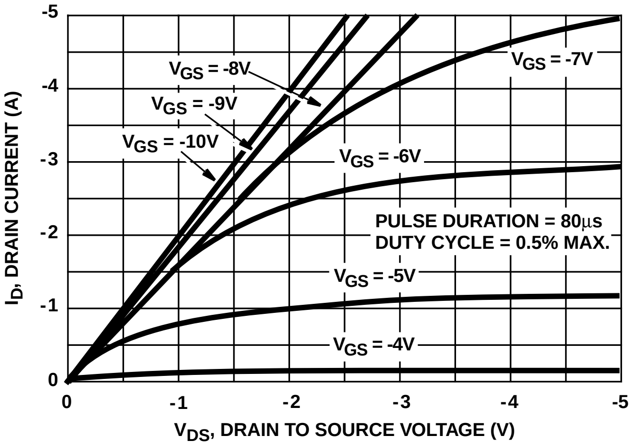


FIGURE 6. SATURATION CHARACTERISTICS

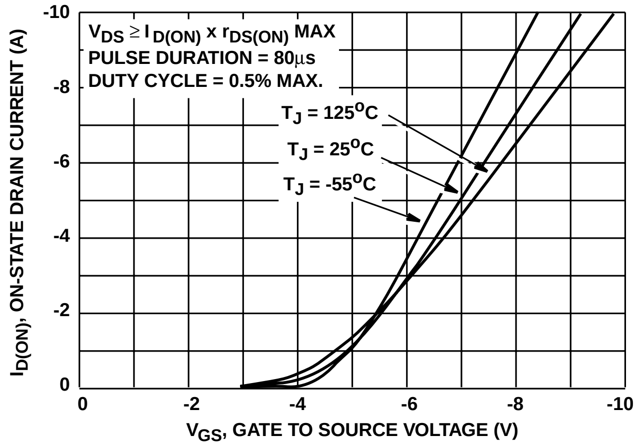


FIGURE 7. TRANSFER CHARACTERISTICS

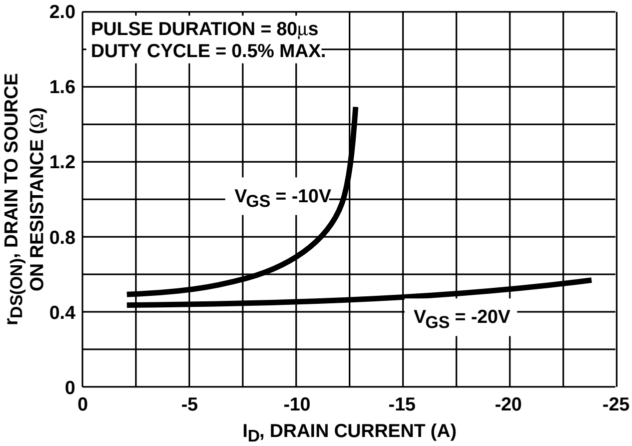


FIGURE 8. DRAIN TO SOURCE ON RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT

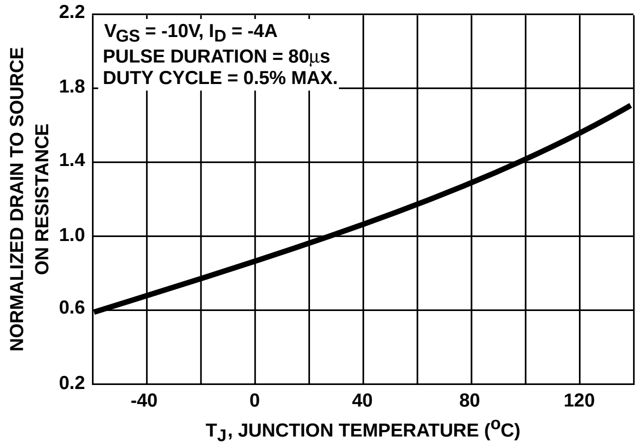


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

Typical Performance Curves Unless Otherwise Specified **(Continued)**

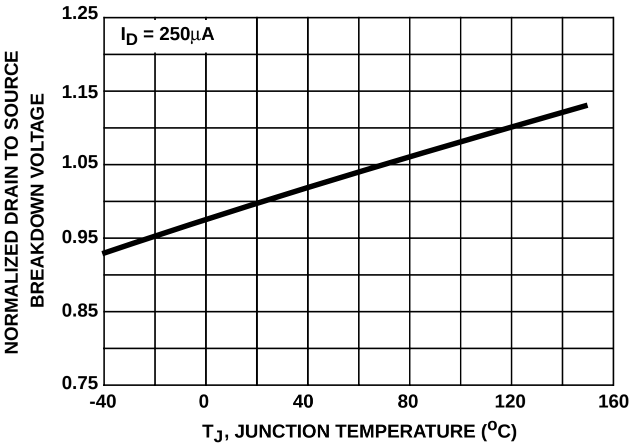


FIGURE 10. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

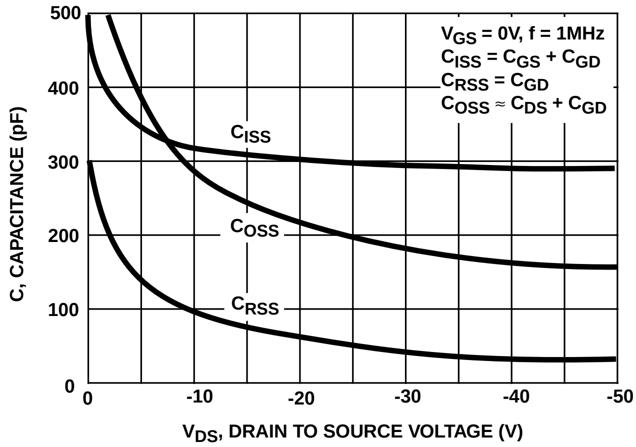


FIGURE 11. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE

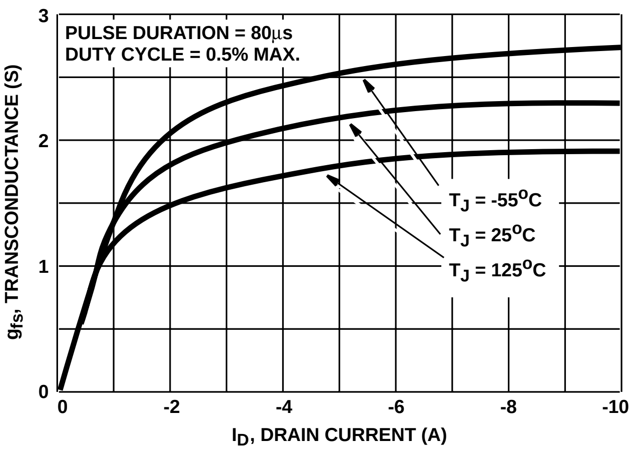


FIGURE 12. TRANSCONDUCTANCE vs DRAIN CURRENT

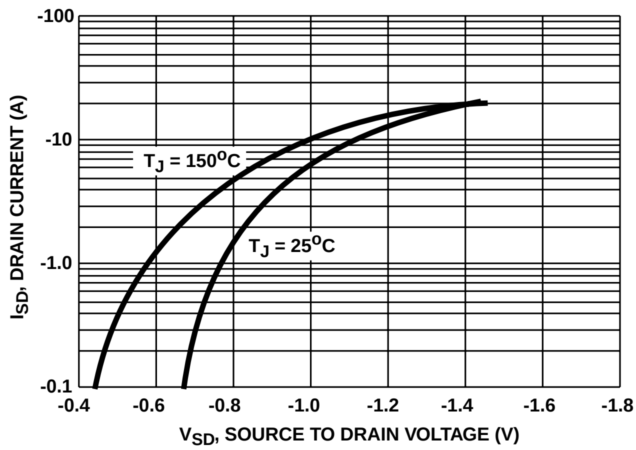


FIGURE 13. SOURCE TO DRAIN DIODE VOLTAGE

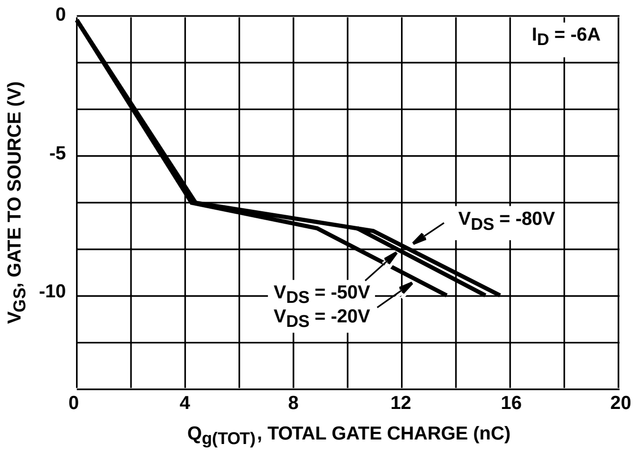


FIGURE 14. GATE TO SOURCE VOLTAGE vs GATE CHARGE